(12) INTERNATIONAL APPLICATION PUBLISHED UNDER THE PATENT COOPERATION TREATY (PCT)

(19) World Intellectual Property Organization
International Bureau

(43) International Publication Date
15 January 2009 (15.01.2009)

PCT

(10) International Publication Number
WO 2009/007003 A1

(51) International Patent Classification:
H01L 21/762 (2006.01)

(21) International Application Number:
PCT/EP2008/005107

(22) International Filing Date: 24 June 2008 (24.06.2008)

(25) Filing Language: English

(26) Publication Language: English

(30) Priority Data:
07290869.2 11 July 2007 (11.07.2007) EP
08290490.5 28 May 2008 (28.05.2008) EP

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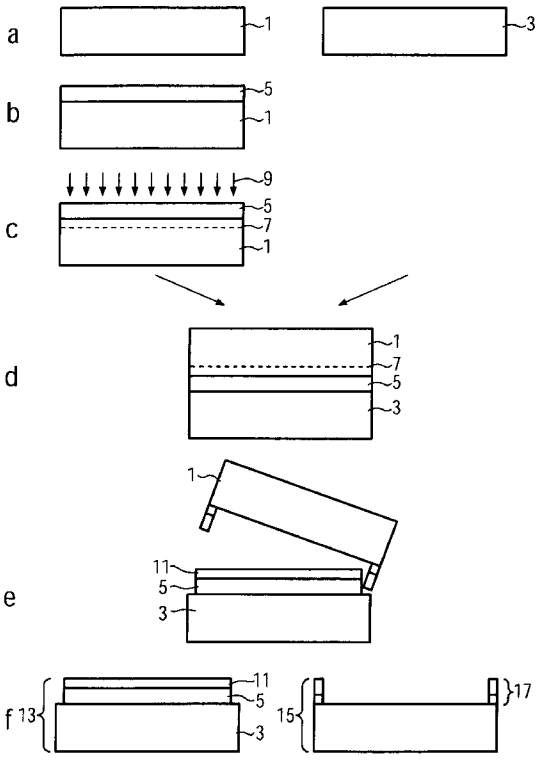
(81) Designated States *(unless otherwise indicated, for every kind of national protection available)*: AE, AG, AL, AM, AO, AT, AU, AZ, BA, BB, BG, BH, BR, BW, BY, BZ, CA, CH, CN, CO, CR, CU, CZ, DE, DK, DM, DO, DZ, EC, EE, EG, ES, FI, GB, GD, GE, GH, GM, GT, HN, HR, HU, ID, IL, IN, IS, JP, KE, KG, KM, KN, KP, KR, KZ, LA, LC, LK, LR, LS, LT, LU, LY, MA, MD, ME, MG, MK, MN, MW, MX, MY, MZ, NA, NG, NI, NO, NZ, OM, PG, PH, PL, PT, RO, RS, RU, SC, SD, SE, SG, SK, SL, SM, SV, SY, TJ, TM, TN, TR, TT, TZ, UA, UG, US, UZ, VC, VN, ZA, ZM, ZW.

(84) Designated States *(unless otherwise indicated, for every kind of regional protection available)*: ARIPO (BW, GH, GM, KE, LS, MW, MZ, NA, SD, SL, SZ, TZ, UG, ZM, ZW), Eurasian (AM, AZ, BY, KG, KZ, MD, RU, TJ, TM), European (AT, BE, BG, CH, CY, CZ, DE, DK, EE, ES, FI, FR, GB, GR, HR, HU, IE, IS, IT, LT, LU, LV, MC, MT, NL,

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(54) Title: METHOD FOR RECYCLING A SUBSTRATE, LAMINATED WATER FABRICATING METHOD AND SUITABLE RECYCLED DONOR SUBSTRATE

Fig. 1



(57) Abstract: The invention relates to a method for recycling a substrate with a step-like residue in a first region of its surface, in particular along the edge of the substrate, which protrudes with respect to the surface of a remaining second region of the substrate, and wherein the first region comprises a modified zone, in particular an ion implanted zone, essentially in a plane corresponding to the plane of the surface of the remaining second region of the substrate and/or chamfered towards the edge of the substrate. To prevent the negative impact of contaminants in subsequent laminated wafer fabricating processes, the recycling method comprises a material removal step which is carried out such that the surface of the substrate in the first region is lying lower than the level of the modified zone before the material removal. The invention also relates to a laminated wafer fabricating method using the recycled substrate and to a recycled substrate in which the surface of a first region lies lower than the surface of the second region.

WO 2009/007003 A1

NO, PL, PT, RO, SE, SI, SK, TR), OAPI (BF, BJ, CF, CG, CI, CM, GA, GN, GQ, GW, ML, MR, NE, SN, TD, TG).

Published:

— *with international search report*

— *before the expiration of the time limit for amending the claims and to be republished in the event of receipt of amendments*

— *with information concerning one or more priority claims considered void*